

FIELD-EFFECT TRANSISTOR

INTRODUCTION

prepared by:

Gyro A. Madrona

Electronics Engineer

TOPIC OUTLINE

JFET Construction

Regions of Operation

Transconductance Curve



JFET CONSTRUCTION



HISTORY



Julius Edgar Lilienfeld

The concept of the field-effect transistor was first proposed by Julius Edgar Lilienfeld in a 1925 patent, but he never built a working device due to material limitations of the era.

technology limitations

HISTORY

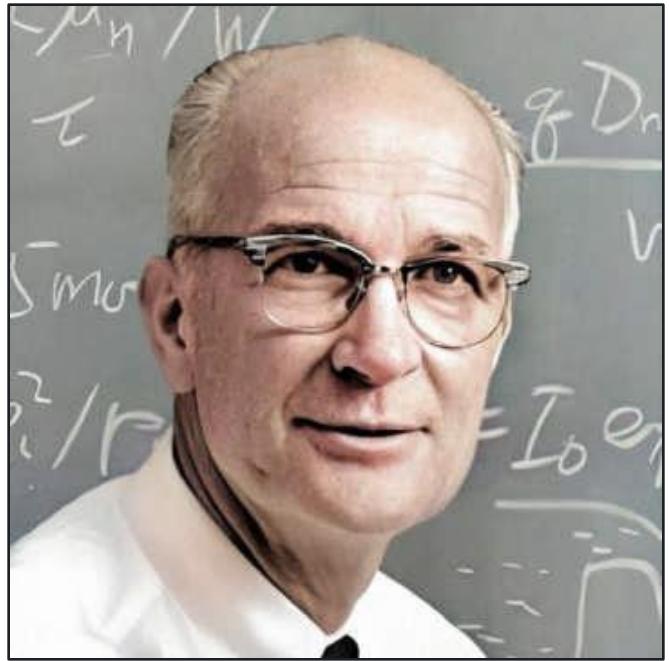


[Dr. Ian Munro Ross](#)

[Dr. George Clement Dacey](#)

They worked on methods to characterize and understand the behavior of field-effect transistors (FETs), which were still experimental at that time (1940s – 1950s). Their contributions were crucial for validating the theoretical principles of FET operation.

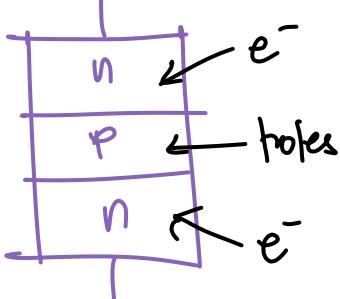
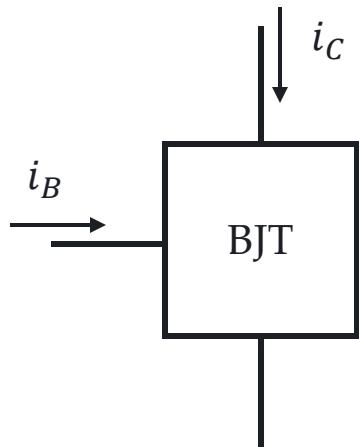
HISTORY



Dr. William Shockley

The first practical junction field-effect transistor (JFET) was successfully built by William Shockley and his team at Bell Labs around 1952. Shockley had theorized about FETs even before inventing the bipolar junction transistor in 1947, but the technology to make them work came later.

BJT VS FET



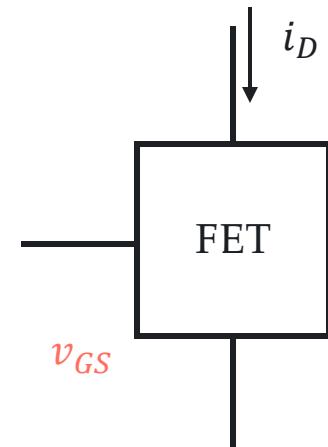
Current-controlled device

Output current (i_C) is controlled by base current (i_B)

Bipolar device

Majority carriers are both electrons and holes

n-type *p-type*



Voltage-controlled device

Output current (i_D) is controlled by gate-to-source voltage (v_{GS})

Unipolar device

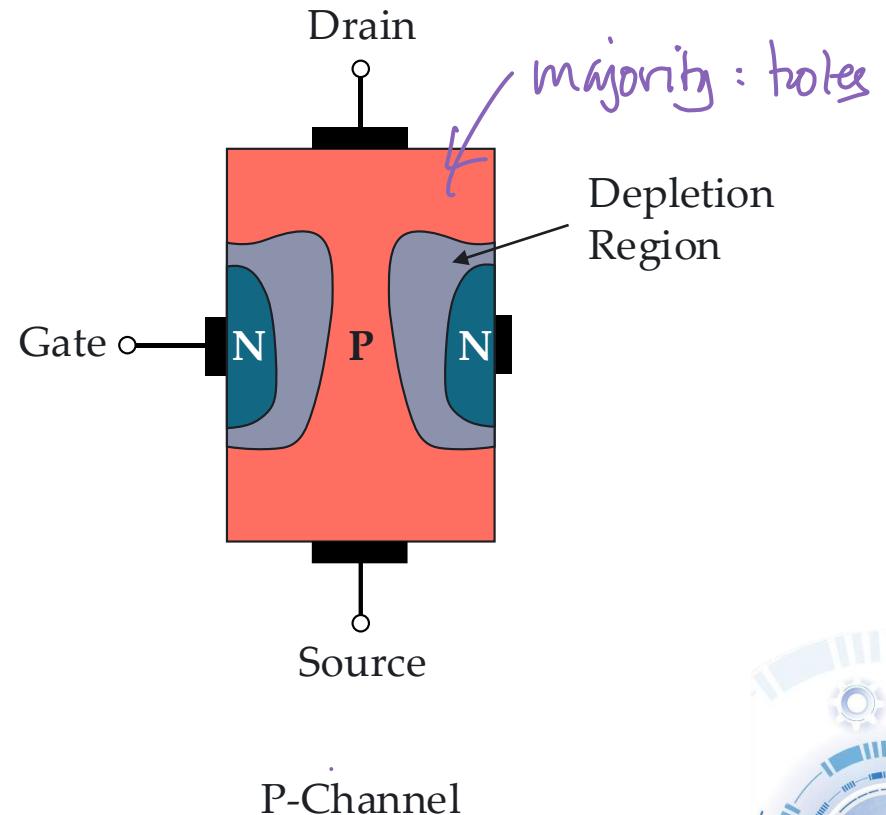
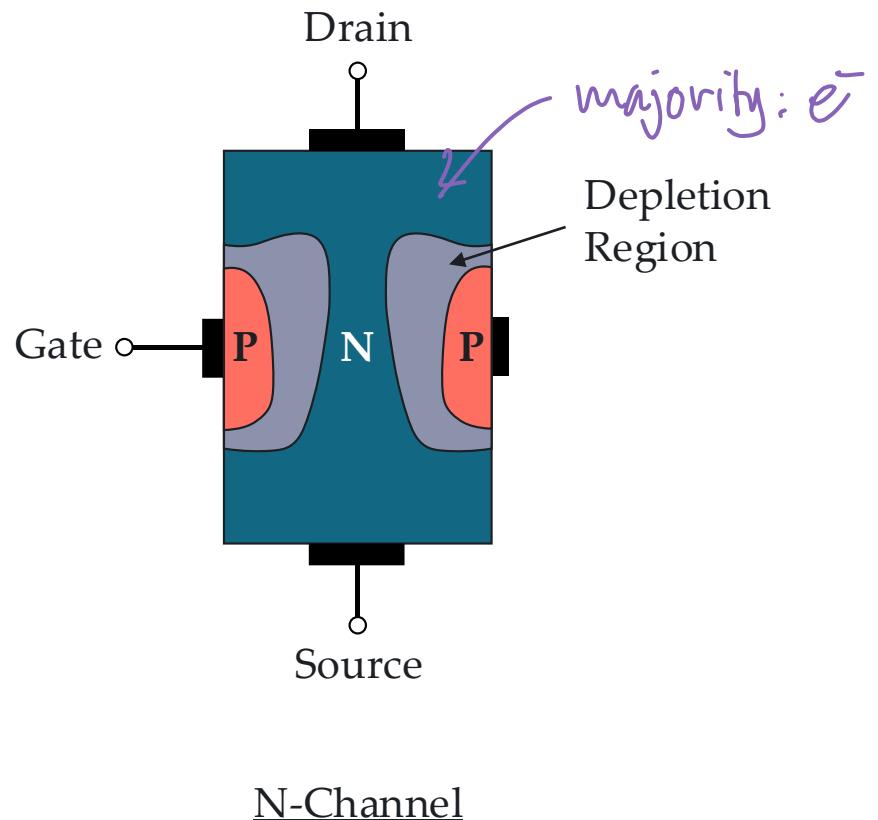
Majority carrier is either electrons (n-channel) or holes (p-channel)



CONSTRUCTION

JFET

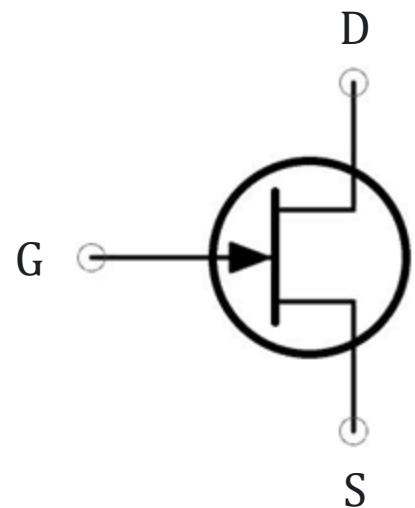
Junction Field-Effect Transistor



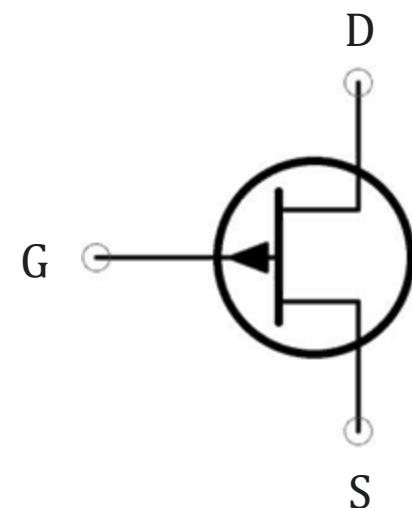
SCHEMATIC SYMBOL

JFET

Junction Field-Effect Transistor



N-Channel

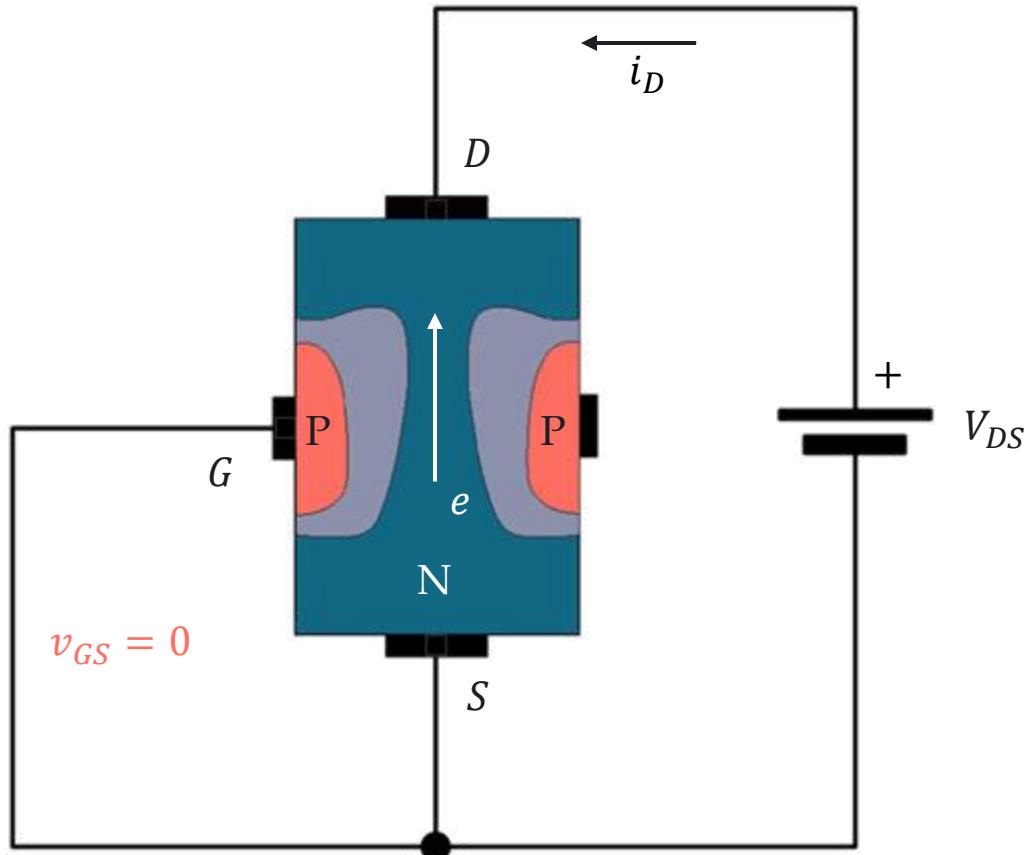


P-Channel

REGIONS OF OPERATION

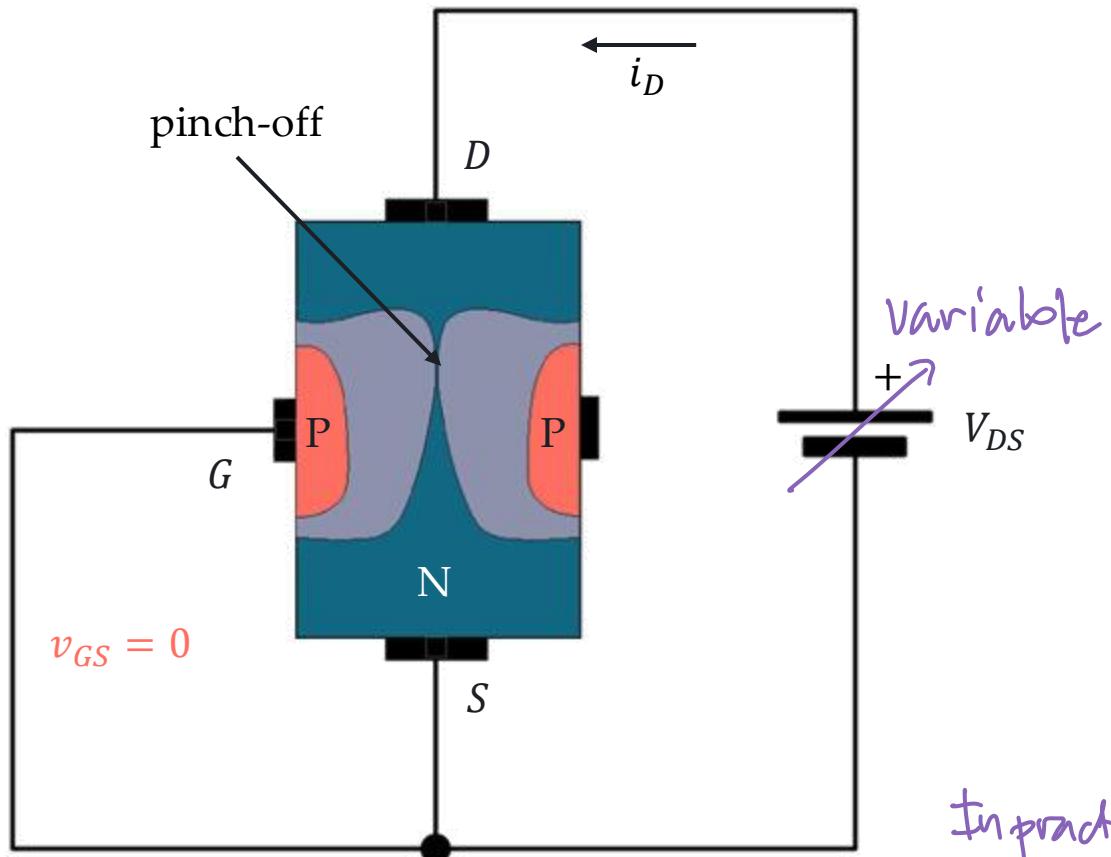


NORMALLY “ON” DEVICE



When v_{GS} is zero, maximum drain (i_D) current flows between the source and the drain.

PINCH-OFF VOLTAGE

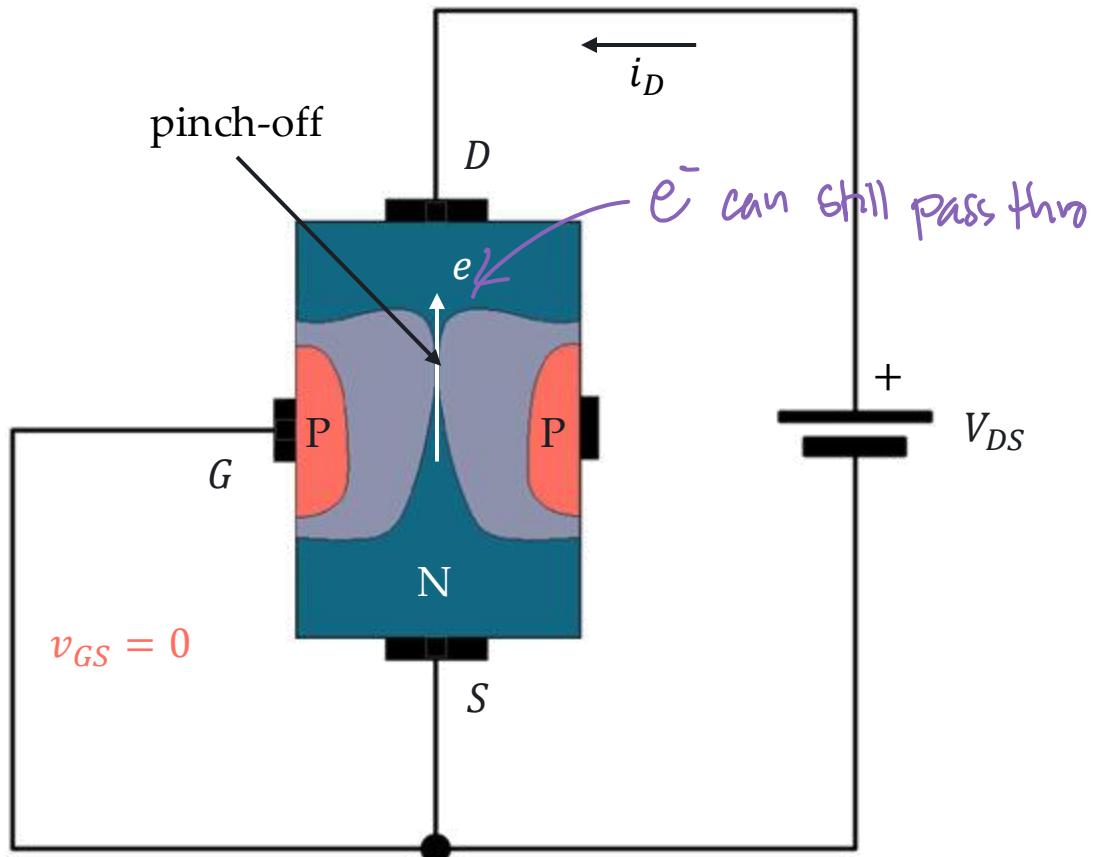


If V_{DS} is increased to a level where it appears that two regions would “touch”, a condition referred to as **pinch-off** will result.

The level of V_{DS} that established this condition is referred to as **pinch-off voltage, V_P** .

In practical application,
 V_{GS} is variable

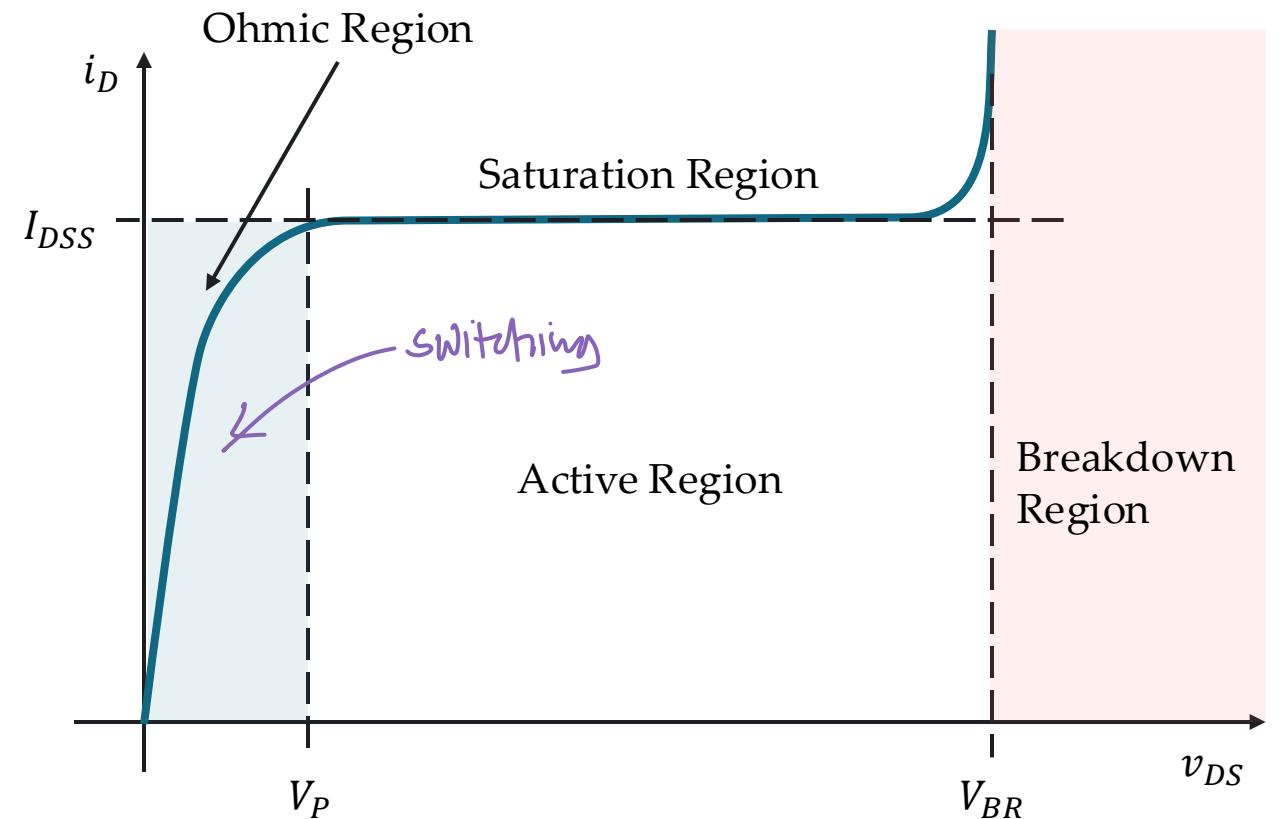
PINCH-OFF VOLTAGE



i_D does not drop off at pinch-off and maintains saturation level defined as I_{DSS} (Drain-to-Source current with a Short-circuit connection from gate to source).

I_{DSS} is the maximum drain current when $v_{GS} = 0$.

DRAIN CURVE



When operated in the ohmic region, a JFET is equivalent to a resistor with a value of approximately:

$$R_{DS} = \frac{V_P}{I_{DSS}}$$

Ohm's law

EXERCISE

An MPF4857 has $V_p = 6V$ and $I_{DSS} = 100\text{ mA}$. What is the ohmic resistance? The gate-source cutoff voltage?

Solution

Ohmic Resistance

$$R_{DS} = \frac{V_p}{I_{DSS}}$$

$$R_{DS} = \frac{6}{100\text{ m}}$$

$$R_{DS} = 60\Omega$$

ans

Gate-source cutoff voltage

$$V_{GS(\text{off})} = -V_p$$

$$V_{GS(\text{off})} = -6V$$

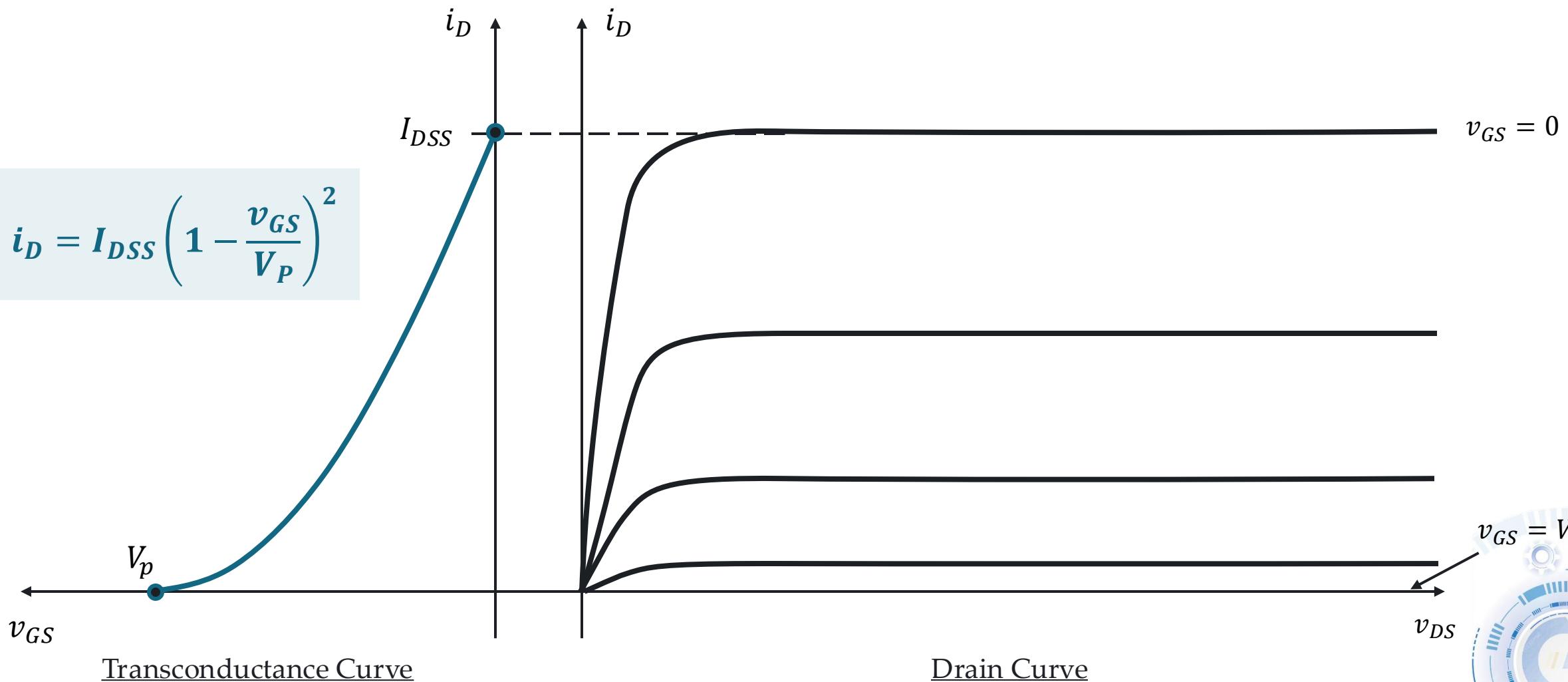
ans

TRANSCONDUCTANCE CURVE

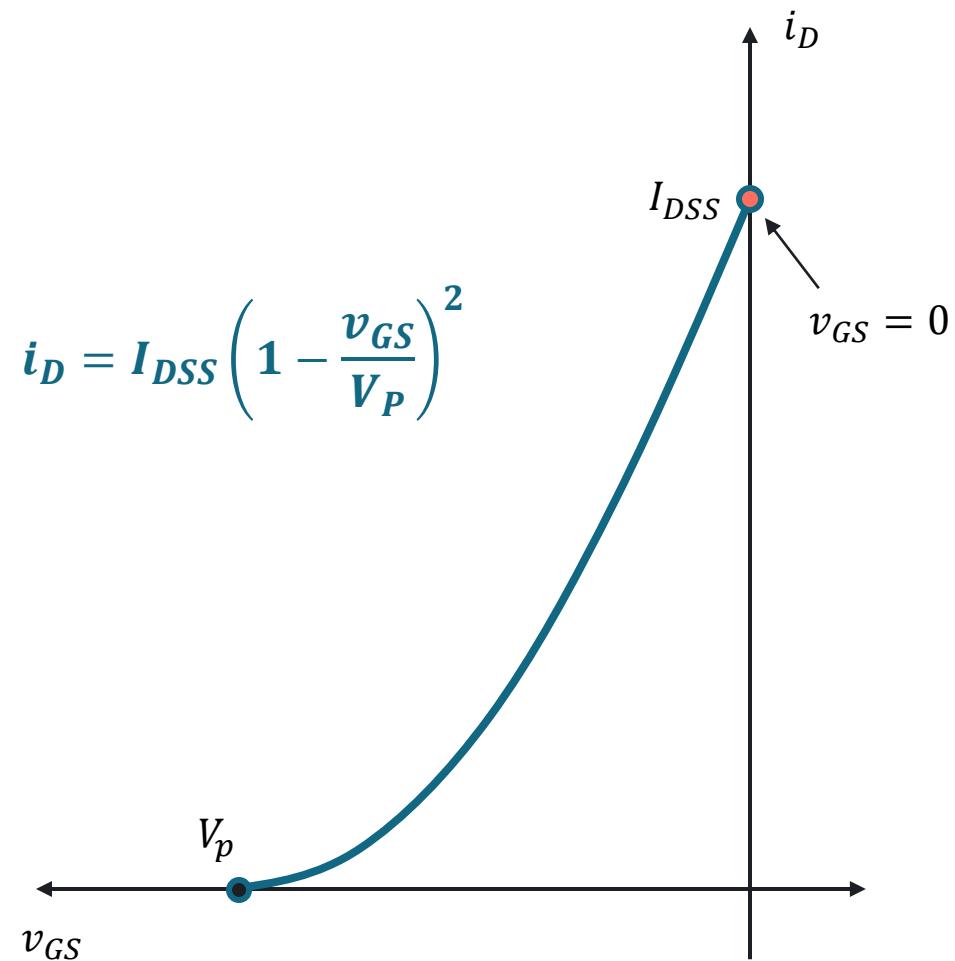


SHOCKLEY'S EQUATION

$$i_D = I_{DSS} \left(1 - \frac{v_{GS}}{V_P} \right)^2$$



TRANSCONDUCTANCE CURVE



$$i_D = I_{DSS} \Big|_{v_{GS}=0}$$

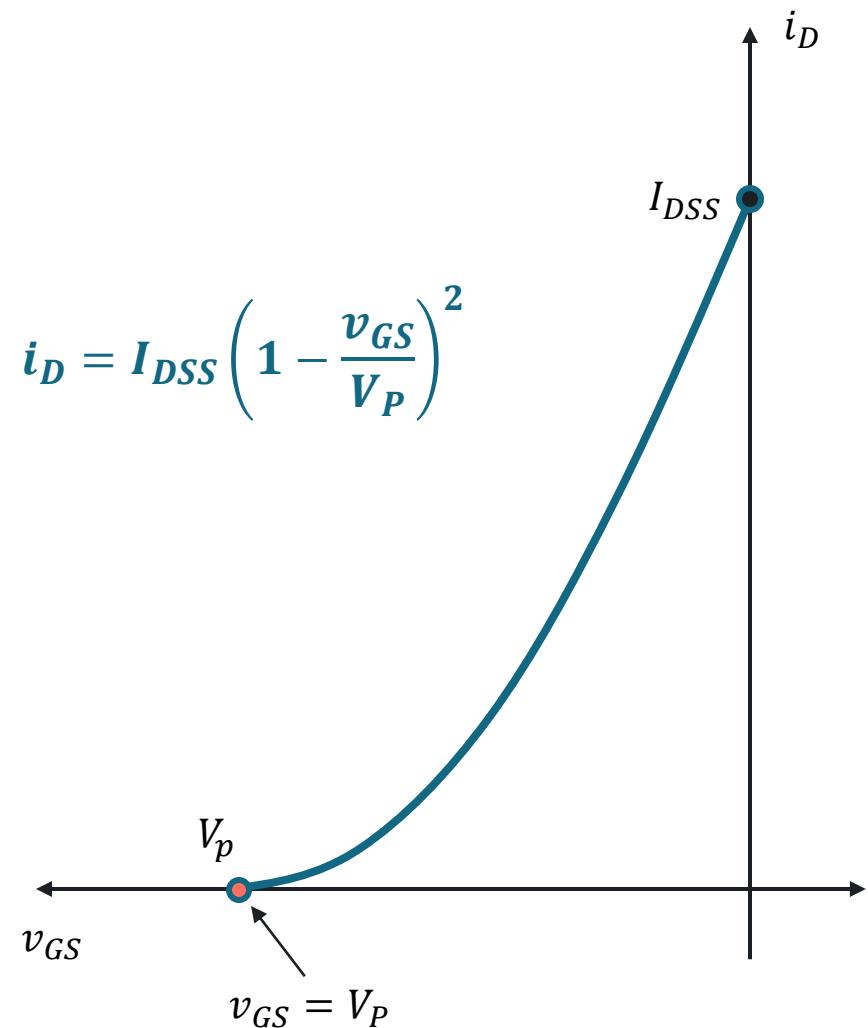
$$i_D = I_{DSS} \left(1 - \frac{v_{GS}}{V_p} \right)^2$$

$$i_D = I_{DSS} (1 - 0)^2$$

$$\underline{i_D = I_{DSS}}$$



TRANSCONDUCTANCE CURVE



$$i_D = 0 \Big|_{v_{GS}=V_p}$$

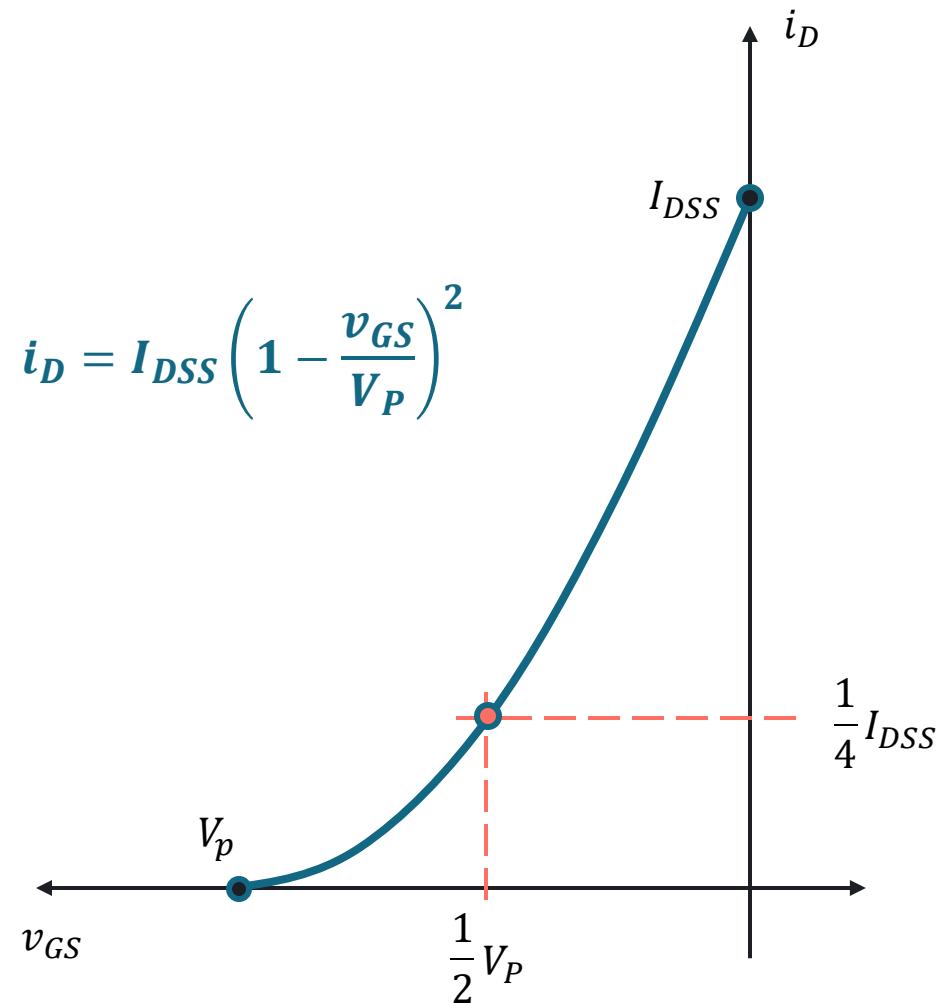
$$i_D = I_{DSS} \left(1 - \frac{v_{GS}}{V_p} \right)^2 \xrightarrow{v_{GS}}$$

$$i_D = I_{DSS} (1 - 1)^2$$

$$\underline{i_D = 0}$$



TRANSCONDUCTANCE CURVE



$$i_D = \frac{1}{4} I_{DSS} \Big|_{v_{GS} = \frac{1}{2}V_p}$$

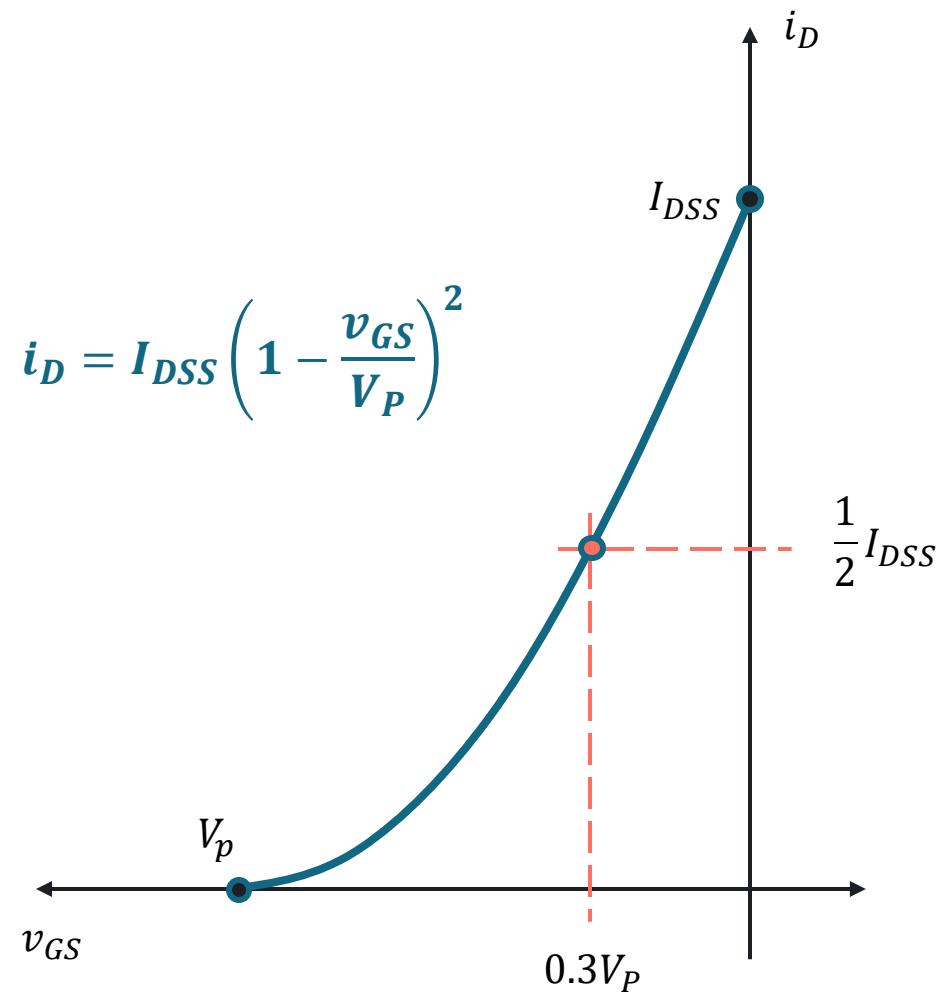
$$i_D = I_{DSS} \left(1 - \frac{v_{GS}}{V_p} \right)^2$$

$$i_D = I_{DSS} (1 - 0.5)^2$$

$$\underline{i_D = 0.25 I_{DSS}}$$



TRANSCONDUCTANCE CURVE



$$v_{GS} = 0.3V_P \Big|_{i_D = \frac{1}{2}I_{DSS}}$$

~~$i_D = I_{DSS} \left(1 - \frac{v_{GS}}{V_P} \right)^2$~~

$$\sqrt{0.5} = \left(1 - \frac{v_{GS}}{V_P} \right)^2$$

$$\frac{v_{GS}}{V_P} = 1 - \sqrt{0.5}$$

$$\underline{v_{GS} = 0.3V_P}$$



EXERCISE

Sketch the transconductance curve defined by

$$I_{DSS} = 12\text{mA} \text{ and } V_P = -6\text{V}.$$

Solution

Let $V_{GS} = 0.5 V_P$

$$i_D = \frac{1}{4} I_{DSS} \quad \Big| \quad V_{GS} = \frac{1}{2} V_P$$

$$i_D = \frac{1}{4} (12\text{m}) \quad \Big| \quad V_{GS} = -3$$

$i_D = 3\text{mA} @ V_{GS} = -3\text{V}$

Let $i_D = 0.5 I_{DSS}$

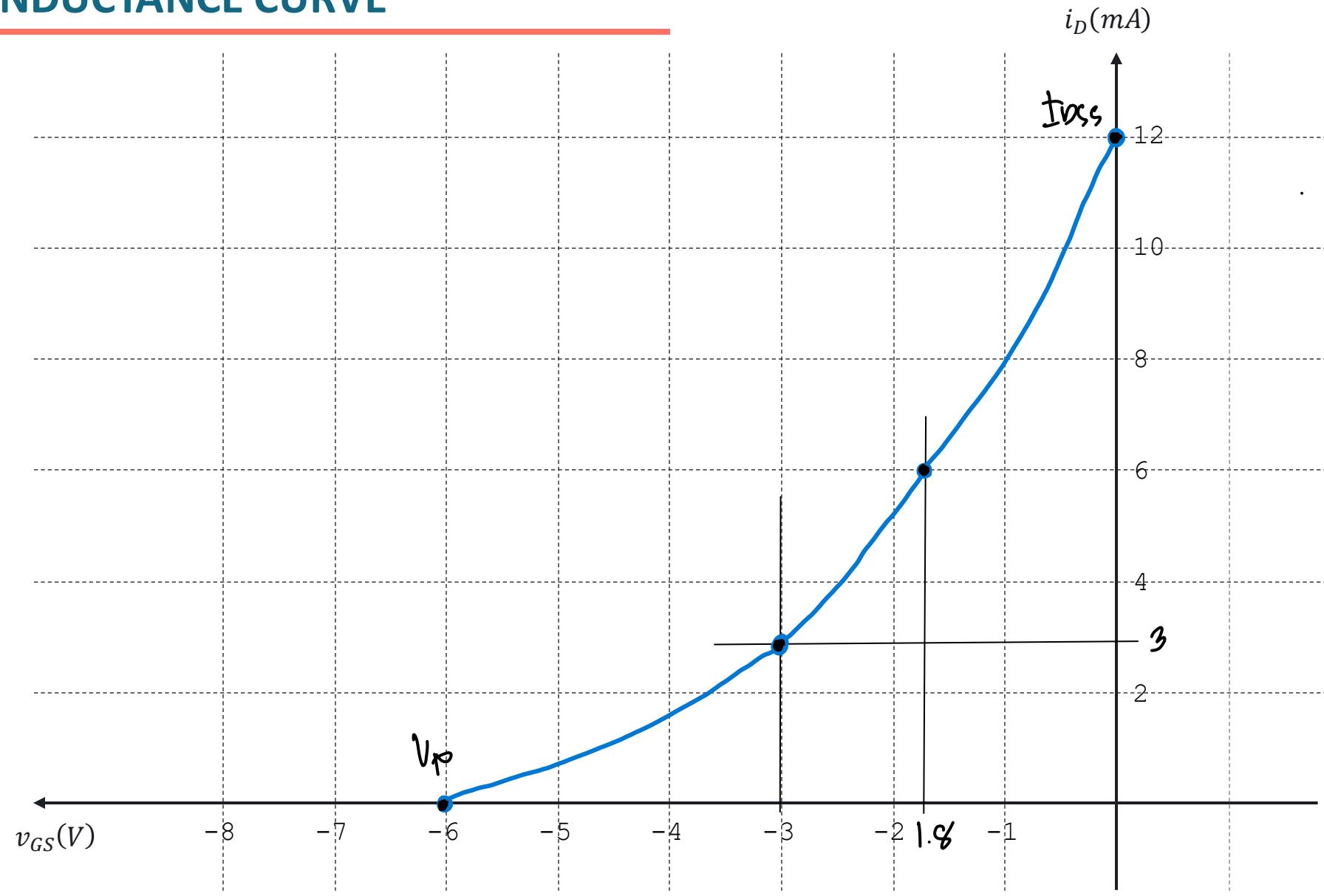
$$V_{GS} = 0.5 V_P \quad \Big| \quad i_D = \frac{1}{2} I_{DSS}$$

$$V_{GS} = 0.5 (-6) \quad \Big| \quad i_D = 6$$

$V_{GS} = -1.8\text{V} @ i_D = 6\text{mA}$



TRANSCONDUCTANCE CURVE



LABORATORY

